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[Erratum]

Erratum to "Effect of Air Exposure on ZnO Thin Film for Electron Transport Layer of Quantum Dot Light-Emitting Diode"

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The original version of this article (Vol. 32, No. 6, pp.455-461, https://doi.org/10.46670/JSST.2023.32.6.455) contained an error in Table 1. The total trap density (N_t) of ZnO thin films with no air exposure should be 1.79×10^{17} cm^{-3}.

Before Correction

Air exposure time	Mobility ($cm^2/V\cdot sec$)	l+1	V_{t-c} (V)	N_t (cm^{-3})
N_2 (No exposure)	2.75×10^{-6}	6.29	1.8	11.79×10^{17}
1 hour	3.56×10^{-4}	3.16	1.4	3.93×10^{17}
1 day	1.48×10^{-4}	4.04	1.5	2.52×10^{17}

After Correction

Air exposure time	Mobility ($cm^2/V\cdot sec$)	l+1	V_{t-c} (V)	N_t (cm^{-3})
N_2 (No exposure)	2.75×10^{-6}	6.29	1.8	1.79×10^{17}
1 hour	3.56×10^{-4}	3.16	1.4	3.93×10^{17}
1 day	1.48×10^{-4}	4.04	1.5	2.52×10^{17}

REFERENCES

[1] E. Seo, K. Lee, J. H. Hwang, D. H. Kim, J. Lim, and D. Lee, "Effect of Air Exposure on ZnO Thin Film for Electron Transport Layer of Quantum Dot Light-Emitting Diode", *J. Sens. Sci. Technol.*, Vol. 32, No. 6, pp. 455-461, 2023.

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